

MOSFET – N-Channel, POWERTRENCH®

100 V, 6.6 A, 28 mΩ

FDT86102LZ

General Description

This N-Channel MOSFET is produced using onsemi's advanced POWERTRENCH process that has been especially tailored to minimize the on-state resistance and switching loss. G-S zener has been added to enhance ESD voltage level.

Features

- Max $r_{DS(on)}$ = 28 mΩ at $V_{GS} = 10$ V, $I_D = 6.6$ A
- Max $r_{DS(on)}$ = 38 mΩ at $V_{GS} = 4.5$ V, $I_D = 5.5$ A
- HBM ESD Protection Level > 6 kV Typical (Note 4)
- Very Low Q_g and Q_{gd} Compared to Competing Trench Technologies
- Fast Switching Speed
- 100% UIL Tested
- This Device is Pb-Free, Halide Free and RoHS Compliant

Applications

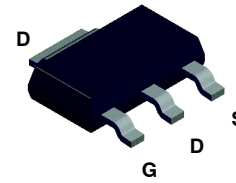
- DC – DC Conversion
- Inverter
- Synchronous Rectifier

Specifications

MOSFET MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

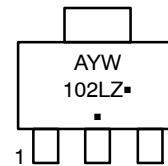
Symbol	Parameter	Ratings	Unit	
V_{DS}	Drain to Source Voltage	100	V	
V_{GS}	Gate to Source Voltage	±20	V	
I_D	Drain Current	-Continuous	6.6	A
		-Pulsed	40	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	84	mJ	
P_D	Power Dissipation	$T_A = 25^\circ\text{C}$ (Note 1a)	2.2	W
		$T_A = 25^\circ\text{C}$ (Note 1b)	1.0	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



SOT-223
CASE 318H

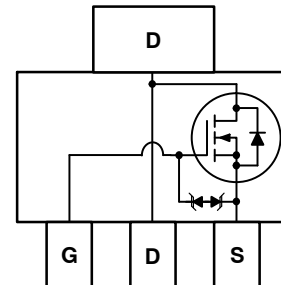
MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- W = Work Week
- 102LZ = Specific Device Code
- = Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT



ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

FDT86102LZ

THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case (Note 1)	12	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	55	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
--------	-----------	-----------------	-----	-----	-----	------

OFF CHARACTERISTICS

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}$, $V_{GS} = 0 \text{ V}$	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C		70		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 80 \text{ V}$, $V_{GS} = 0 \text{ V}$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$			± 10	μA

ON CHARACTERISTICS

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu\text{A}$	1.0	1.4	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C		-6		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}$, $I_D = 6.6 \text{ A}$		22	28	m Ω
		$V_{GS} = 4.5 \text{ V}$, $I_D = 5.5 \text{ A}$		27	38	
		$V_{GS} = 10 \text{ V}$, $I_D = 6.6 \text{ A}$, $T_J = 125^\circ\text{C}$		36	46	
g_{FS}	Forward Transconductance	$V_{DS} = 5 \text{ V}$, $I_D = 6.6 \text{ A}$		26		S

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = 50 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$		1118	1490	pF
C_{oss}	Output Capacitance			181	245	pF
C_{rss}	Reverse Transfer Capacitance			7.5	15	pF
R_g	Gate Resistance			0.5		Ω

SWITCHING CHARACTERISTICS

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50 \text{ V}$, $I_D = 6.6 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_{GEN} = 6 \Omega$		6.6	14	ns
t_r	Rise Time			1.9	10	ns
$t_{d(off)}$	Turn-Off Delay Time			19	31	ns
t_f	Fall Time			2.2	10	ns
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0 \text{ V to } 10 \text{ V}$, $V_{DD} = 50 \text{ V}$, $I_D = 6.6 \text{ A}$		17	25	nC
		$V_{GS} = 0 \text{ V to } 4.5 \text{ V}$, $V_{DD} = 50 \text{ V}$, $I_D = 6.6 \text{ A}$		8.3	12	
Q_{gs}	Gate to Source Charge	$V_{DD} = 50 \text{ V}$, $I_D = 6.6 \text{ A}$		2.6		nC
Q_{gd}	Gate to Drain "Miller" Charge	$V_{DD} = 50 \text{ V}$, $I_D = 6.6 \text{ A}$		2.2		nC

DRAIN-SOURCE DIODE CHARACTERISTICS

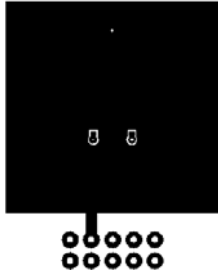
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}$, $I_S = 6.6 \text{ A}$ (Note 2)		0.82	1.3	V
		$V_{GS} = 0 \text{ V}$, $I_S = 1.0 \text{ A}$ (Note 2)		0.68	1.2	
t_{rr}	Reverse Recovery Time	$I_F = 6.6 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$		40	64	ns
Q_{rr}	Reverse Recovery Charge	$I_F = 6.6 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$		36	58	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

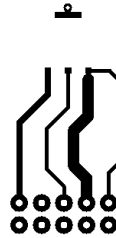
FDT86102LZ

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 55°C/W when mounted on a 1 in² pad of 2 oz copper



b. 118°C/W when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μ s, Duty cycle < 2.0%.
3. Starting $T_J = 25^\circ\text{C}$, $L = 1$ mH, $I_{AS} = 13$ A, $V_{DD} = 90$ V, $V_{GS} = 10$ V.
4. The diode connected between gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

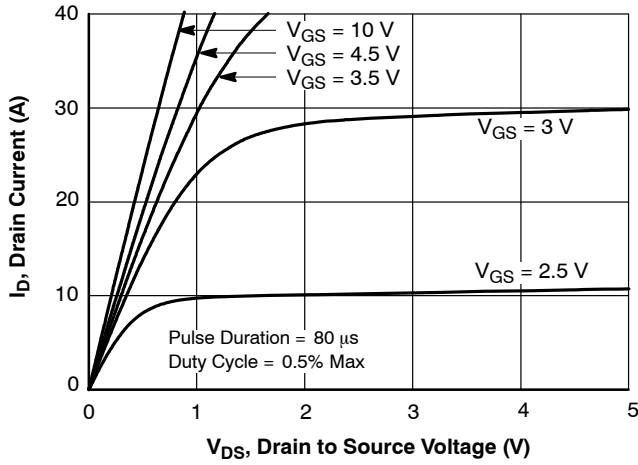


Figure 1. On Region Characteristics

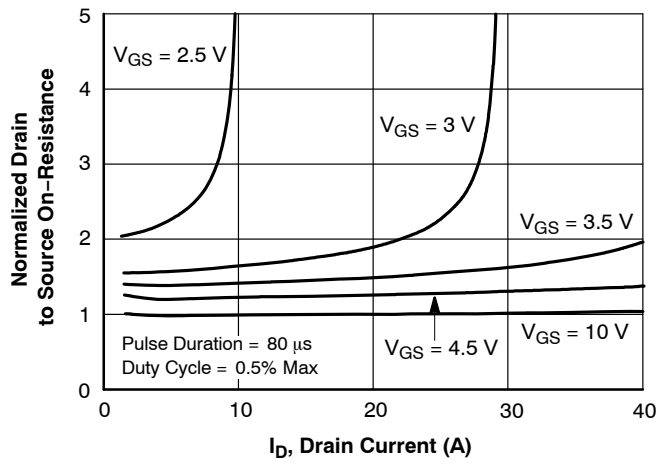


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

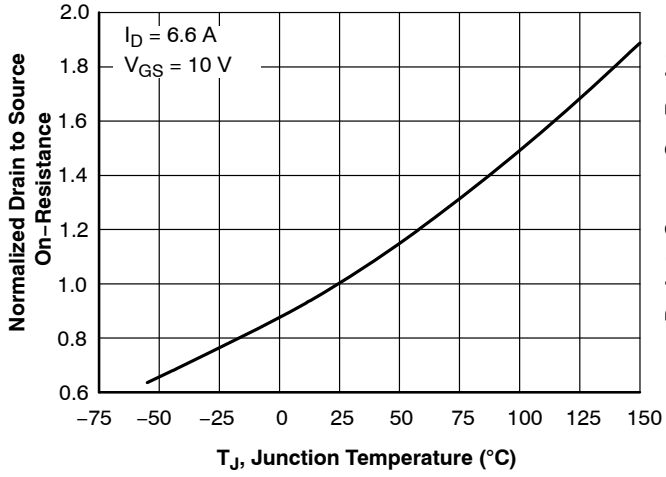


Figure 3. Normalized On Resistance vs. Junction Temperature

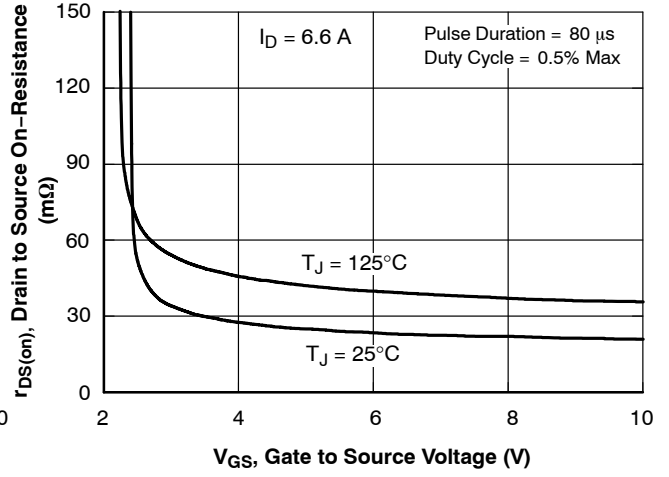


Figure 4. On-Resistance vs. Gate to Source Voltage

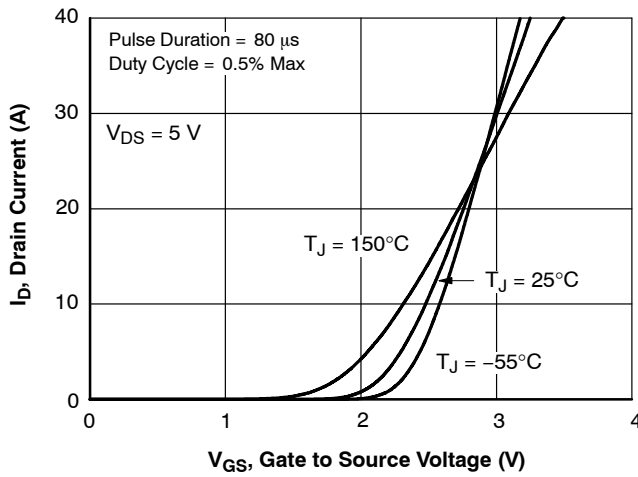


Figure 5. Transfer Characteristics

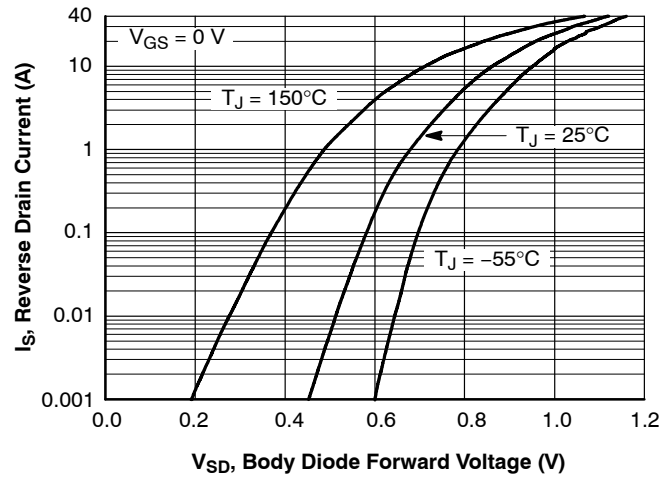


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

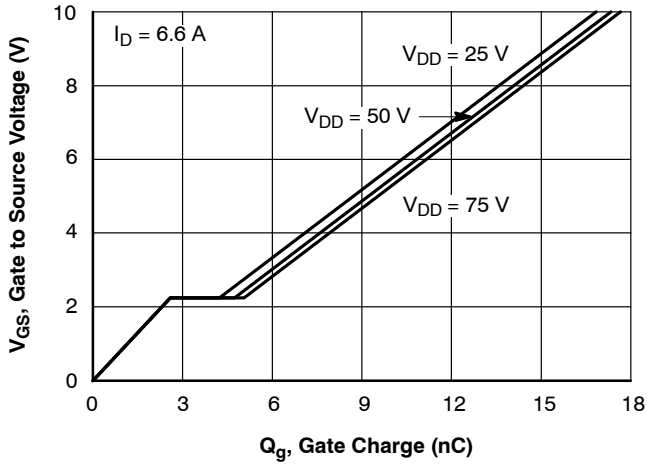


Figure 7. Gate Charge Characteristics

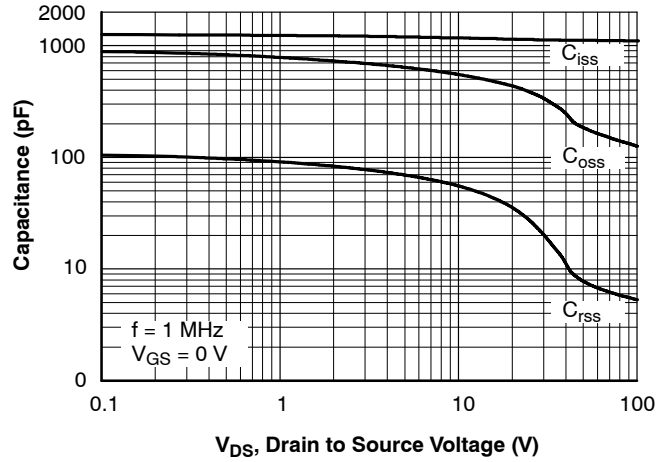


Figure 8. Capacitance vs. Drain to Source Voltage

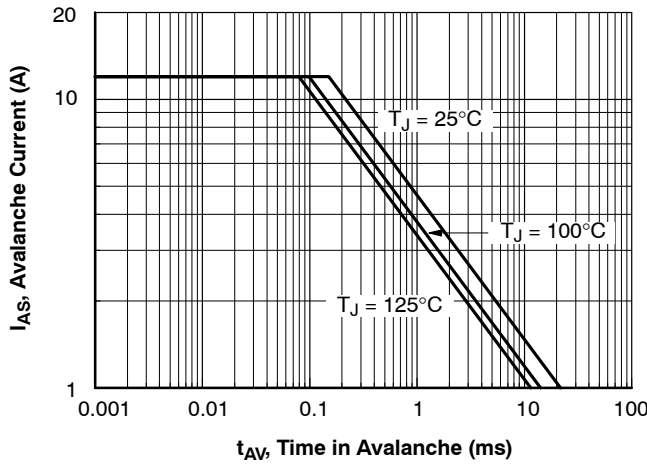


Figure 9. Unclamped Inductive Switching Capability

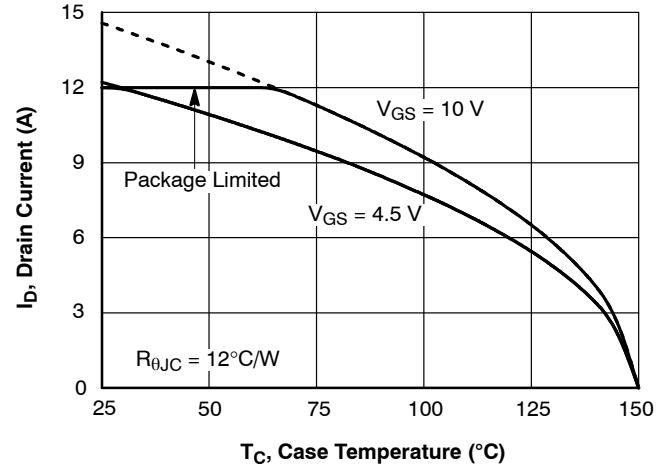


Figure 10. Maximum Continuous Drain Current vs Case Temperature

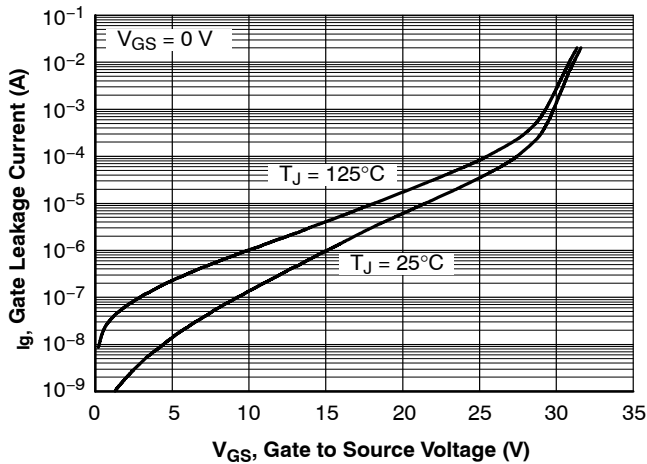


Figure 11. Gate Leakage Current vs Gate to Source Voltage

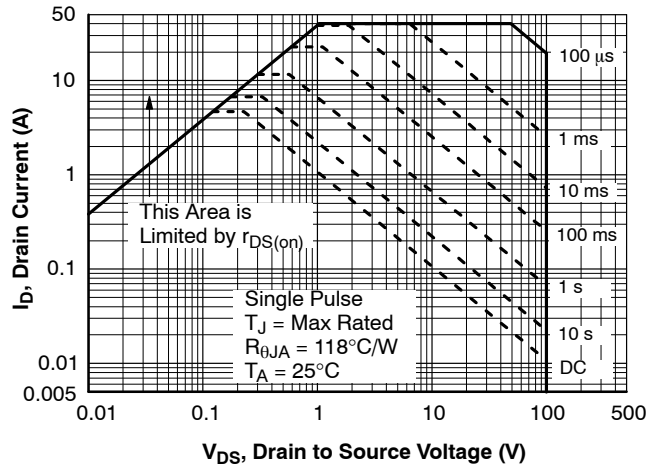


Figure 12. Forward Bias Safe Operating Area

FDT86102LZ

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

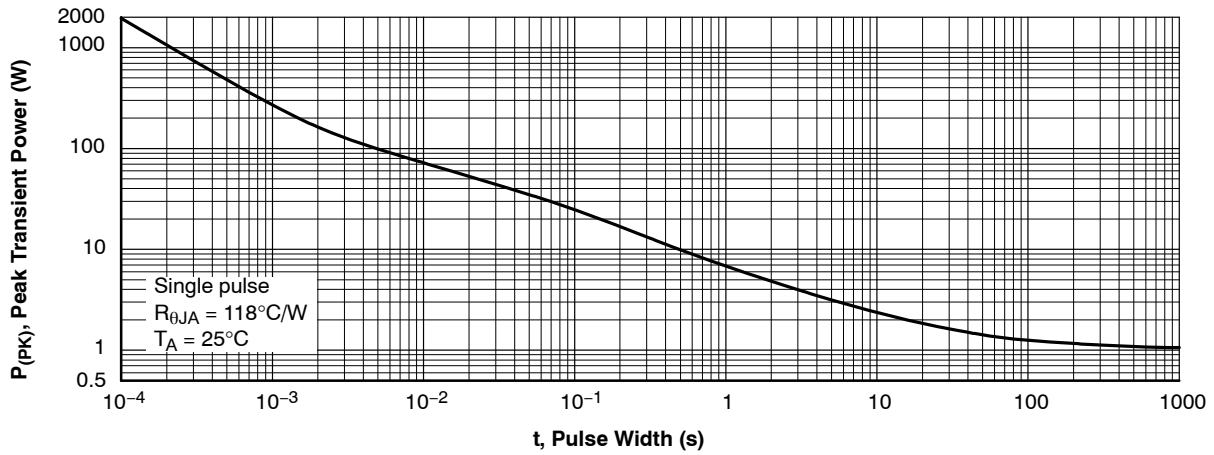


Figure 13. Single Pulse Maximum Power Dissipation

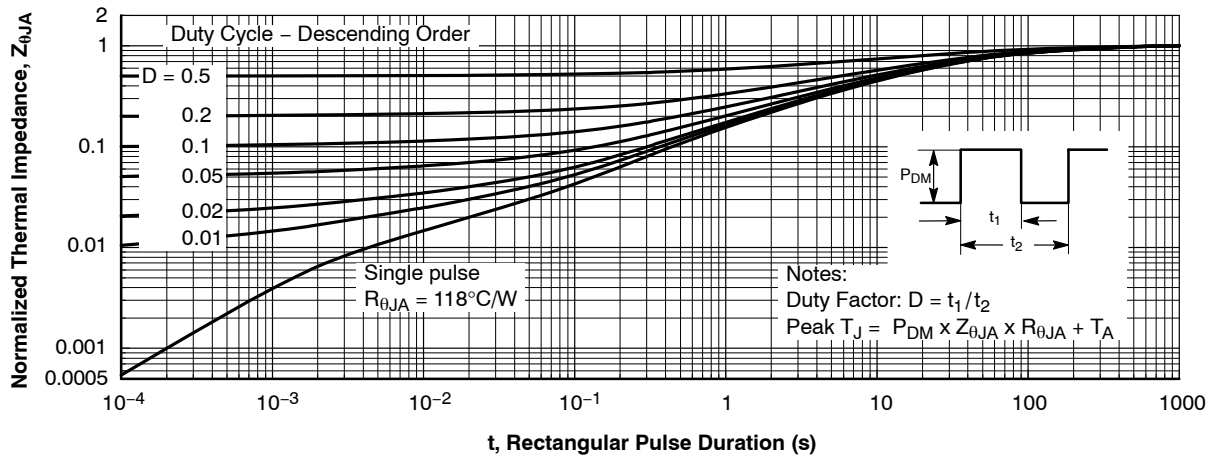


Figure 14. Junction-to-Ambient Transient Thermal Response Curve

ORDERING INFORMATION

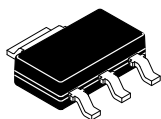
Device	Device Marking	Package Type	Shipping [†]
FDT86102LZ	102LZ	SOT-223 (Pb-Free)	4000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

POWERTRENCH is a registered trademark of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

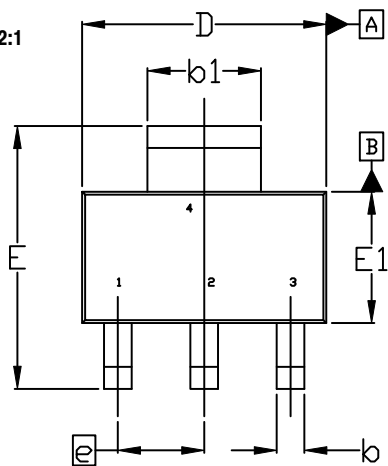
ON Semiconductor®



SOT-223
CASE 318H
ISSUE B

DATE 13 MAY 2020

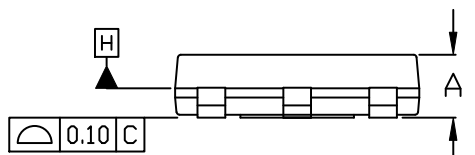
SCALE 2:1



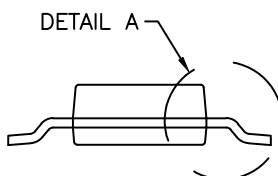
TOP VIEW

$\Phi 0.10 \text{ (M)}$ C A B

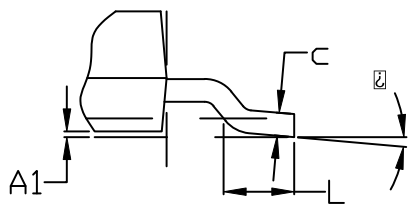
NOTE 7



SIDE VIEW



END VIEW

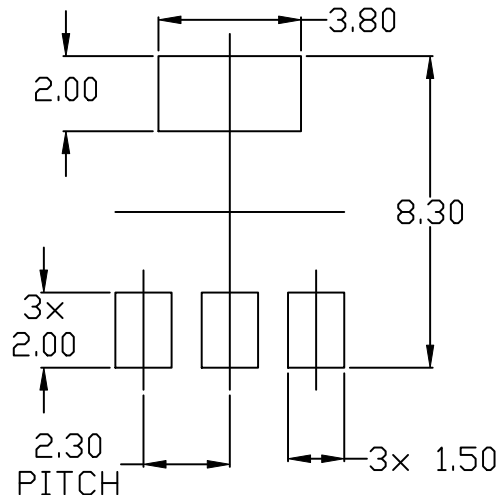


DETAIL A

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D & E1 ARE DETERMINED AT DATUM H. DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. SHALL NOT EXCEED 0.23mm PER SIDE.
4. LEAD DIMENSIONS b AND b1 DO NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION IS 0.08mm PER SIDE.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
7. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

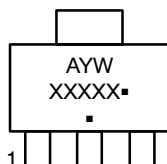
DIM	MILLIMETERS		
	MIN.	NDM.	MAX.
A	---	---	1.80
A1	0.02	0.06	0.11
b	0.60	0.74	0.88
b1	2.90	3.00	3.10
c	0.24	---	0.35
D	6.30	6.50	6.70
E	6.70	7.00	7.30
E1	3.30	3.50	3.70
e	2.30 BSC		
L	0.25	---	---
\square	0°	---	10°



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

GENERIC MARKING DIAGRAM*



- A = Assembly Location
- Y = Year
- W = Work Week
- XXXXX = Specific Device Code
- = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98ASH70634A	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOT-223	PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT

North American Technical Support:
Voice Mail: 1 800-282-9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative